

# **PHPT61010NY**

# 100 V, 10 A NPN high power bipolar transistor 20 March 2015

**Product data sheet** 

# 1. General description

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT61010PY

#### 2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

# 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	100	V
I <sub>C</sub>	collector current		-	-	10	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	20	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 10 A; $I_B$ = 1 A; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C; pulsed	-	25	37	mΩ



100 V, 10 A NPN high power bipolar transistor

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	Е	emitter		В
3	Е	emitter	000	, M
4	В	base		E sym123
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	- Sylli123

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PHPT61010NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT61010NY	1010NAB

100 V, 10 A NPN high power bipolar transistor

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	100	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	100	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	7	V
I <sub>C</sub>	collector current			-	10	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	20	Α
I <sub>B</sub>	base current			-	1	Α
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.5	W
			[2]	-	3.7	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

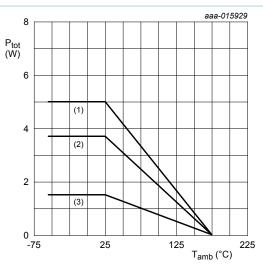
<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

<sup>[3]</sup> Device mounted on an ceramic PCB; Al<sub>2</sub>O<sub>3</sub>, standard footprint.

<sup>[4]</sup> Power dissipation from junction to mounting base.

## 100 V, 10 A NPN high power bipolar transistor



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ang a)	thermal resistance	[2	[1]	-	-	100	K/W
	from junction to		<u>[2]</u>	-	-	41	K/W
	ambient		<u>[3]</u>	-	-	30	K/W
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

#### 100 V, 10 A NPN high power bipolar transistor

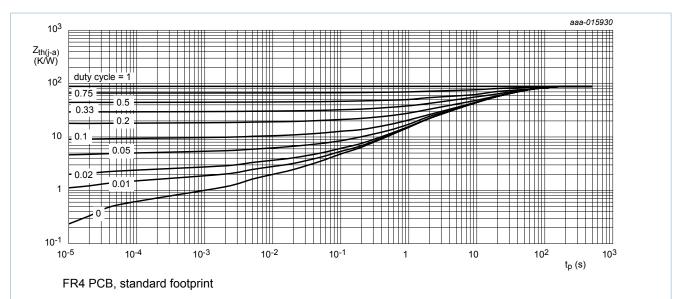


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

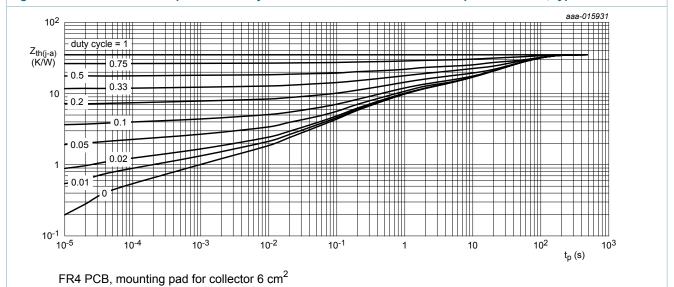


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

100 V, 10 A NPN high power bipolar transistor

# 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 80 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 80 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 80 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 7 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 2 V; $I_{C}$ = 0.5 A; $T_{amb}$ = 25 °C	150	275	-	
		$V_{CE} = 2 \text{ V}; I_{C} = 1 \text{ A}; t_{p} \le 300 \mu\text{s};$ $\delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	150	270	-	
		$V_{CE} = 2 \text{ V}; I_{C} = 5 \text{ A}; t_{p} \le 300 \mu\text{s};$ $\delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	60	110	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 10 A; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C; pulsed	25	50	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 1 A; $I_B$ = 50 mA; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_{amb}$ = 25 °C; pulsed	-	30	50	mV
		$I_C$ = 5 A; $I_B$ = 0.5 A; pulsed; $t_p \le 300 \ \mu s$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	120	180	mV
			$I_{C}$ = 10 A; $I_{B}$ = 1 A; pulsed; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	250	370
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C = 10 \text{ A}; I_B = 1 \text{ A}; t_p \le 300 \text{ µs};$ $\delta \le 0.02; T_{amb} = 25 ^{\circ}C; \text{ pulsed}$	-	25	37	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = 1 A; $I_B$ = 50 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	0.95	V
		$I_C$ = 5 A; $I_B$ = 0.5 A; pulsed; $t_p \le 300 \ \mu s$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	1.15	V
		$I_C = 10 \text{ A}; I_B = 1 \text{ A}; \text{ pulsed}; t_p \le 300 \mu\text{s};$ $\delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	-	-	1.35	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = 2 V; $I_{C}$ = 0.5 A; $T_{amb}$ = 25 °C	-	-	0.9	V
t <sub>d</sub>	delay time	$V_{CC}$ = 12.5 V; $I_C$ = 5 A; $I_{Bon}$ = 250 mA;	-	25	-	ns
t <sub>r</sub>	rise time	$I_{Boff}$ = -250 mA; $T_{amb}$ = 25 °C	-	365	-	ns
t <sub>on</sub>	turn-on time		-	390	-	ns
t <sub>s</sub>	storage time		-	280	-	ns
t <sub>f</sub>	fall time		-	220	-	ns
t <sub>off</sub>	turn-off time		-	500	-	ns

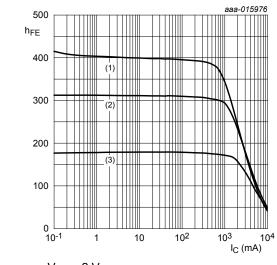
PHPT61010NY

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#### 100 V, 10 A NPN high power bipolar transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 500 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	145	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	40	70	pF



 $V_{CE} = 2 V$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb}$  = 25 °C

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 4. DC current gain as a function of collector current; typical values

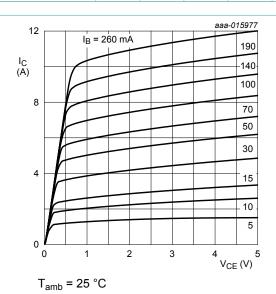
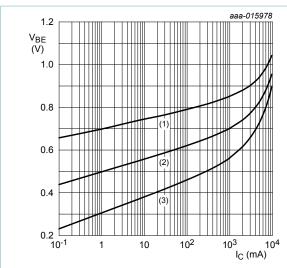


Fig. 5. Collector current as a function of collectoremitter voltage; typical values

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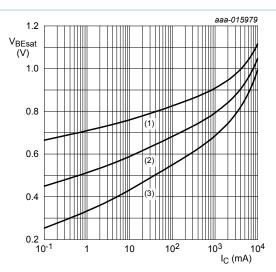
$$V_{CE} = 2 V$$

(1) 
$$T_{amb} = -55$$
 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



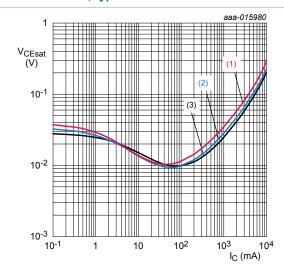
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



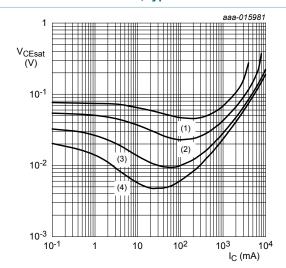
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 100$$

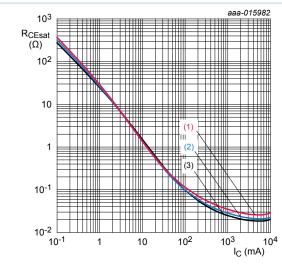
(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 20$$

$$(4) I_C/I_B = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

## 100 V, 10 A NPN high power bipolar transistor



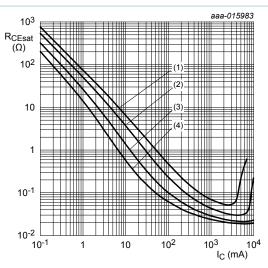
$$I_C/I_B = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

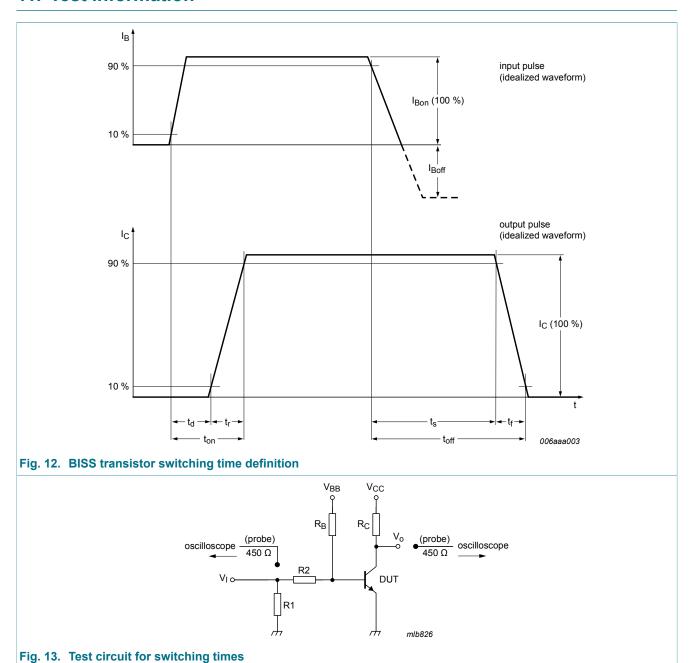
(3) 
$$I_C/I_B = 20$$

(4) 
$$I_{\rm C}/I_{\rm B} = 10$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

100 V, 10 A NPN high power bipolar transistor

# 11. Test information

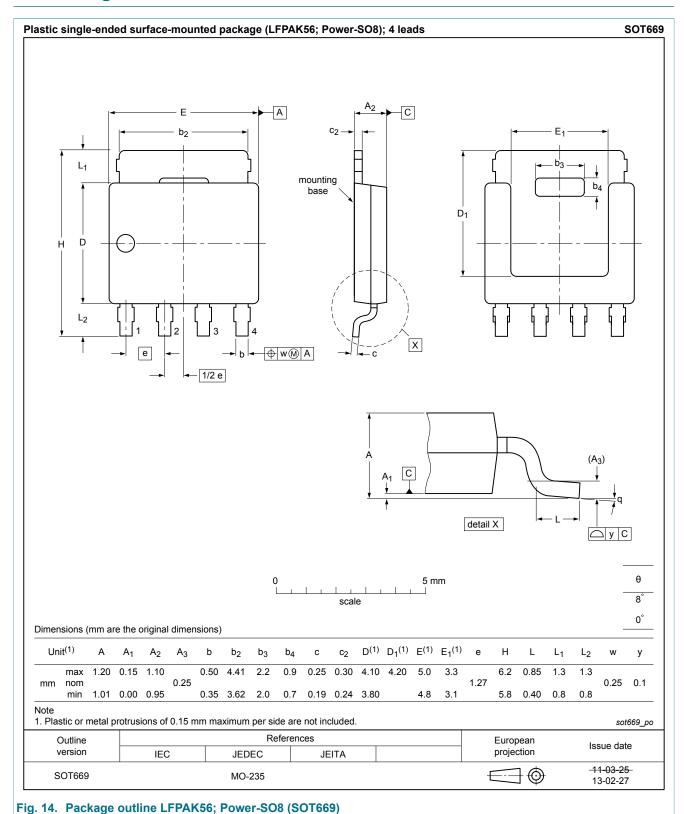


## 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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# 12. Package outline



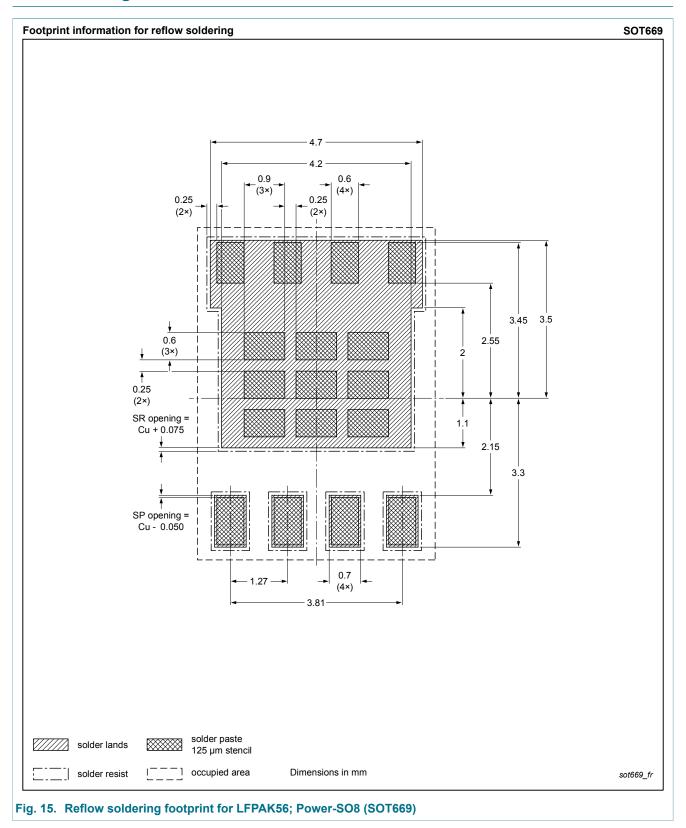
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# 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61010NY v.1	20150320	Product data sheet	-	-

#### 100 V, 10 A NPN high power bipolar transistor

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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## 100 V, 10 A NPN high power bipolar transistor

# 16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	10
11.1	Quality information	10
12	Package outline	11
13	Soldering	12
14	Revision history	13
15	Legal information	14
15.1	Data sheet status	14
15.2	Definitions	14
15.3	Disclaimers	14
15.4	Trademarks	15

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